Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	60	mA
I_H	I_T=500mA	-	-	50	mA
dV/dt	V_D=400V Gate Open T_j=125	700	-	-	V/μs
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25	-	5	-	μs
t_{off}		-	80	-	

STATIC CHARACTERISTICS

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ORDERING INFORMATION

J	CT	6	12	H
JieJie Microelectronics Co., Ltd.	SCRs	6:V_{DRM} /V_{RRM} ≥ 600V	$I_{T(RMS)}$:12A	H:TO-251

MARKING

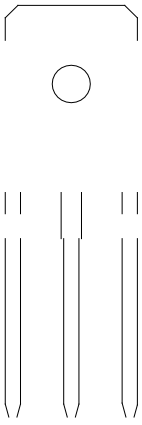


FIG.1: Maximum power dissipation versus RMS on-state current

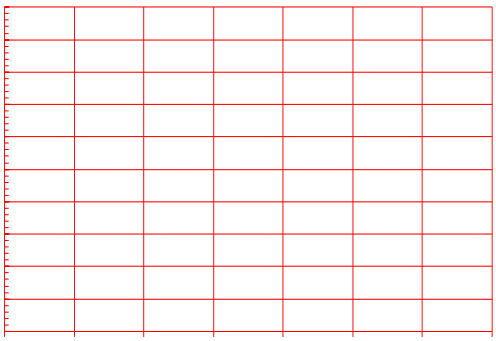


FIG.2: RMS on-state current versus case temperature

JCT612H **Jie**

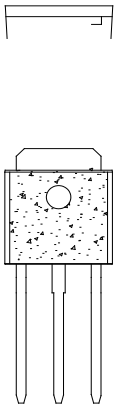
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT612H	600	15	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



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